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Stocking Distributor

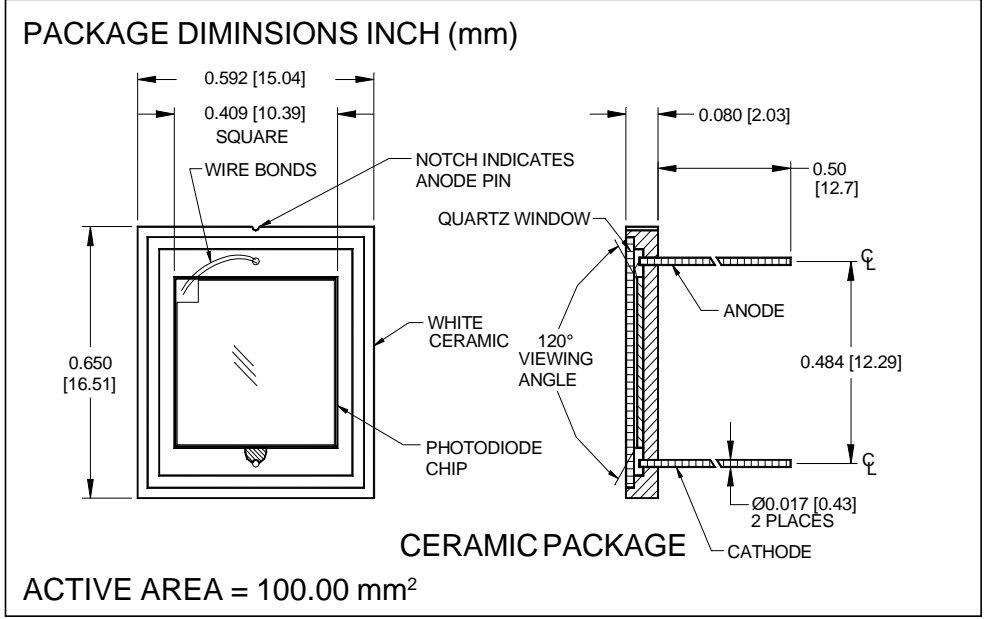
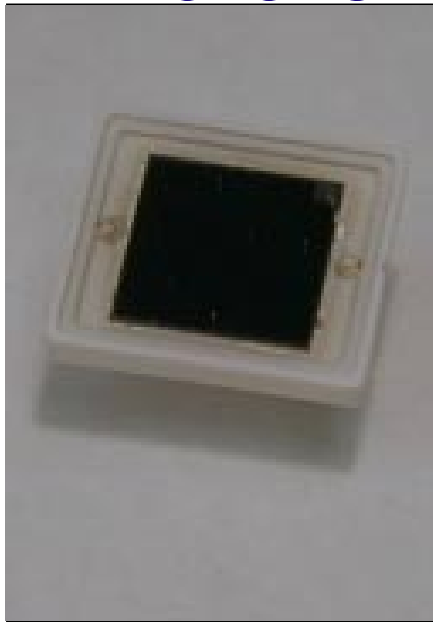
Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Advanced Photonix, Inc.](#)
[PDU-V110](#)

For any questions, you can email us directly:

sales@integrated-circuit.com

Silicon Photodiode, U.V. Enhanced Photovoltaic
Type PDU-V110



FEATURES

- Low noise
- U.V. enhanced
- High shunt resistance
- Quartz windows

DESCRIPTION

The **PDU-V110** is a silicon, PIN planar diffused, U.V. enhanced photodiode. Ideal for low noise photovoltaic applications. Packaged in low profile ceramic substrate with a quartz window.

APPLICATIONS

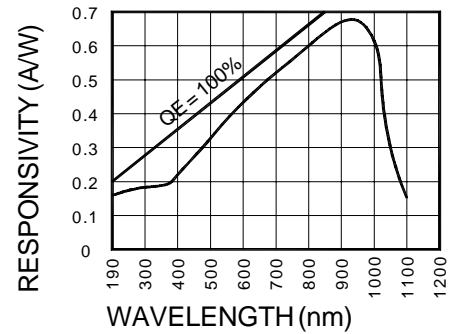
- Spectrometers
- Fluorescent analysers
- U.V. meters
- Colorimeters

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		75	V
T _{STG}	Storage Temperature	-20	+80	°C
T _O	Operating Temperature Range	-20	+60	°C
T _S	Soldering Temperature*		+220	°C
I _L	Light Current		0.5	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	0.9	1.2		mA
I _D	Dark Current	H = 0, V _R = 10 mV		200	333	pA
R _{SH}	Shunt Resistance	H = 0, V _R = 10 mV	30	50		MΩ
TC _{RSH}	R _{SH} Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
C _J	Junction Capacitance	H = 0, V _R = 0 V**		10,000	12,000	pF
λ _{range}	Spectral Application Range	Spot Scan	190		1100	nm
R	Responsivity	V _R = 0 V, λ = 254 nm	.12	.18		A/W
V _{BR}	Breakdown Voltage	I = 10 μA	5	10		V
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		2.0x10 ⁻¹⁴		W/√Hz
tr	Response Time	RL = 1 KΩ V _R = 0 V		2000		nS